

The features of the intrinsic photoconductivity spectra of silver-doped zinc sulphide

KAZIM A. ALIYEV¹, SAADAT O. MAMMADOVA¹, AYTAN N. SULTANOVA^{1*},
AHMAD I. AHMADOV¹, ICABIKA Z. SARDAROVA²
and ABDULAGA N. GURBANOV^{2**}

¹University of Niš, Faculty of Technology, Bulevar Oslobođenja 124, 16000 Leskovac, Serbia
and ²University of Niš, Faculty of Medicine, Blvd. Dr Zorana Đinđića 81, 18000 Niš, Serbia

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Abstract: The intrinsic photoconductivity of silver-doped zinc sulphide (ZnS:Ag) was investigated. It was shown that doping with silver leads to significant modifications in the electronic structure and optical properties of ZnS due to the formation of localized energy levels within the band gap. Mechanical polishing of the sample surface resulted in the appearance of an additional photoconductivity maximum near the fundamental absorption edge, which gradually disappears during sample ageing. These effects are attributed to the compensation of donor and acceptor states, as well as to changes in charge carrier recombination mechanisms. The dependence of the photoconductivity spectrum on ageing time, the applied electric field, and the position of illumination relative to the contacts was established. The results are explained by variations in the lifetime of non-equilibrium charge carriers with depth. A qualitative model describing the photoconductivity spectra is proposed, taking into account the influence of silver compensation on the energy structure of ZnS. The proposed model provides insight into the photoconductive mechanisms and supports the development of ZnS-based optoelectronic materials.

Keywords: photoconductivity spectra; absorption coefficient; optoelectronic material.

INTRODUCTION

The great importance of modern research on photoconductivity is reflected in the recent rapid growth of interest in all areas of solid-state physics and chemistry.^{1–5} Silver alloying in single crystals leads to significant compensation and results in high sensitivity to radiation.^{6–10}

The main interest in ZnS:Ag is due to the fact that its photoconductivity excitation spectrum coincides with the emission spectrum of serial GaAs-based LEDs,

*,** Corresponding authors. E-mail: (*)aytansultanova@bsu.edu.az ; (**)qabdulaga@mail.ru
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which allows ZnS to be considered a promising material for the manufacture of high-performance resistor opt couplers.^{11–18} The reasons for the high photosensitivity of ZnS:Ag and CdS:Ag samples are not fully understood, but there is evidence of the presence of two levels in the forbidden band gap of these semiconductor sulphides, spaced 0.3 eV apart^{12–17} and located above the top of the valence band.^{19–21} The authors explored the idea of a possible relation between the indicated levels and the localization features of silver in the ZnS lattice to explain the appearance of an additional photoconductivity maximum in the region of the fundamental absorption edge.^{22–24} It is assumed that silver impurities exhibit similar behavior in the investigated semiconductor sulphides.^{25–30}

EXPERIMENTAL

For silver alloying, zinc sulphide grown by the Czochralski method with an electron concentration of $9.2 \times 10^{14} \text{ cm}^{-3}$ was used. Diffuse saturation of silver was carried out using a silver film applied to both surfaces in vacuum-sealed quartz ampoules evacuated to 10^{-5} Torr at temperatures of 800–900 °C. The diffusion time 1–10 h. After annealing, the ampoules were quenched in cold water and the samples were ground with abrasive powders and polished with diamond paste. Hall effect measurements of the free charge carrier concentration in annealed samples indicated that alloying enables the formation of both high-resistivity ($n = 2.4 \times 10^8 - 1 \times 10^9 \text{ cm}^{-3}$) and low-resistivity ($n = 1.4 \times 10^{15} \text{ cm}^{-3}$) materials. Contacts made of liquid Zn, Cd eutectic were applied to the polished surface of the samples in the form of two parallel strips, 2.2–3 mm long, with a gap between them. The photoconductivity signal was measured in the constant field mode using a modulation technique with synchronous detection at a modulation frequency of 8–400 Hz. For the study, high-quality samples were used in order to achieve a photocurrent that significantly exceeds the dark current when illuminated.

RESULTS AND DISCUSSION

Immediately after mechanical polishing of the sample surface, the photoconductivity spectrum exhibits two distinct maxima in the region of the fundamental absorption edge (Fig. 1). The short-wavelength maximum gradually disappears during storage under ambient conditions and is no longer observed after approximately two days. A similar effect is observed after thermal annealing, indicating that the additional peak is associated with surface-related states.

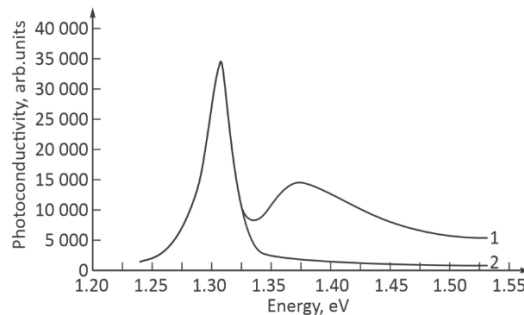


Fig. 1. Photoconductivity spectrum of ZnS:Ag immediately after polishing and after two days. Experimental data; 1 – after polishing at 250 V; 2 – after 50 h at a voltage of 250 V.

Fig. 2 shows the spectral dependence of the photoconductivity of Ag-doped ZnS single crystals as a function of photon energy in the region close to the fundamental absorption edge. Fig. 2 shows the photoconductivity spectra for 60 and 450 V.

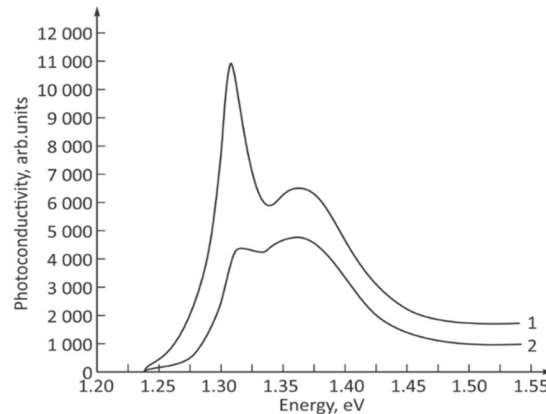
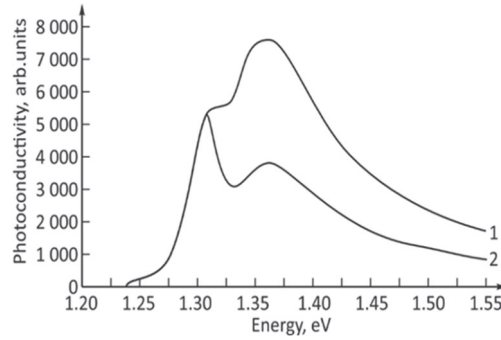


Fig. 2. Photoconductivity spectrum of a polished ZnS:Ag sample at different voltages. Experimental data at: 1 – 60 V; 2 – 450 V.

As seen from the spectra, the photoconductivity begins to increase rapidly when the photon energy approaches the fundamental absorption edge of ZnS. This behavior is associated with the generation of electron-hole pairs due to inter-band optical transitions. A pronounced maximum is observed in the short-wavelength region near approximately 1.30–1.32 eV. This peak can be attributed to intrinsic photoconductivity related to electronic transitions involving defect levels or localized states in the band gap introduced by silver doping. Two curves are presented in Fig. 2, corresponding to different surface conditions of the sample. Curve 1 exhibits a significantly higher photoconductivity signal compared to curve 2. This difference indicates that surface treatment strongly affects the photoconductive response of the crystal. Mechanical polishing modifies the surface defect structure and may create additional surface states that participate in charge carrier generation or recombination processes. After the main maximum, the photoconductivity gradually decreases with increasing photon energy. This behavior can be explained by changes in the efficiency of carrier generation, recombination processes, and carrier transport in the crystal. Overall, the observed spectral features demonstrate that both bulk defect states and surface-related states contribute to the formation of the intrinsic photoconductivity spectra in Ag-doped ZnS crystals. The results confirm that surface conditions play an important role in determining the magnitude and shape of the photoconductivity response.

It was noted that when the beam was focused near the negative contact, the short-wave peak predominated, whereas focused near the positive contact, the

94 long-wave peak predominated (Fig. 3). The interval between the start of the two
 95 experiments was no more than 10 minutes.



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Fig. 3. Photoconductivity spectrum of a ZnS:Ag sample immediately after polishing with the focusing beam near the positive and negative contacts at a voltage of 200 V. Experimental data for field focusing 1 – near the negative contact, 2 – near the positive contact.

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Previously, the observation of additional extrema beyond the fundamental absorption band edge in the ZnS:Ag photoconductivity spectra has been explained.²

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Let us consider a sample model consisting of several layers. We assume that in ZnS:Ag the quantum yield η is constant in each layer, and the change in mobility from layer to layer is small.² Then the photoconductivity, $\Delta\sigma$, of the entire sample can be described by the following equation:

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$$\begin{aligned} \Delta\sigma(h\nu) = & Q_1(1 - \exp(-\alpha t_1)) + Q_2 \exp(-\alpha t_1)(1 - \exp(-\alpha t_2)) + \\ & + Q_3 \exp(-\alpha t_1) \exp(-\alpha t_2)(1 - \exp(-\alpha t_3)) + \\ & + Q_4 \exp(-\alpha t_1) \exp(-\alpha t_2) \exp(-\alpha t_3)(1 - \exp(\alpha(d - t_1 - t_2 - t_3))) \end{aligned} \quad (1)$$

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where Q_i is a coefficient proportional to the lifetime for each layer; $\alpha = f(h\nu)$ is a performance dependence of the absorption coefficient of ZnS; t_1 is the layer thickness; d is the sample thickness. Q_1 characterizes the contribution of fast recombination processes occurring in the near-surface layer of the crystal. Q_2 describes the trapping and recombination of charge carriers through localized states associated with surface defects. Q_3 represents the contribution of recombination processes occurring in the bulk region of the crystal. Q_4 characterizes the transport of photogenerated charge carriers into deeper layers of the crystal and delayed recombination processes. These parameters are used to fit the shape of the photoconductivity spectra and make it possible to evaluate the relative influence of different recombination mechanisms.

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The absorption coefficient α of zinc sulphide was measured independently and the result presented in Fig. 4 is in good agreement with previously reported data.³ Regions of weak and strong absorption were approximated. In the region of the

fundamental absorption, as the energy of light quanta increases, the absorption coefficient increases significantly, which leads to a decrease in the penetration depth of light. For the energy range from 1.20 to 1.50 eV, the sample can be conditionally divided into 4 layers.

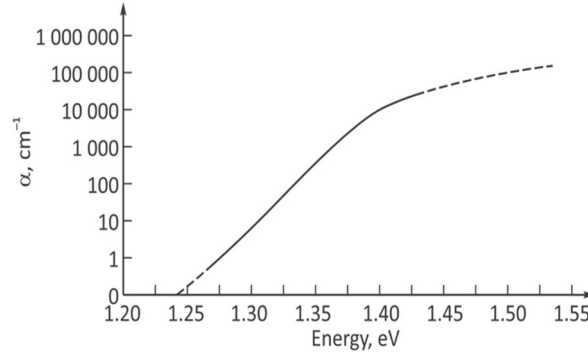


Fig. 4. Spectral dependence of the absorption coefficient of zinc sulphide.

Eq. (1) describes the photoconductivity spectra after polishing for ageing times from 0 to 50 h. The standard deviation did not exceed 4.285×10^{-3} . The values of the obtained parameters of Eq. (1) are given in Table I.

TABLE I Measurement data for the Q -parameters and thickness values t_1-t_4

t_1-t_4	Q_1	Q_2	Q_3	Q_4	$t_1 / \mu\text{m}$	$t_2 / \mu\text{m}$	$t_3 / \mu\text{m}$	$t_4 / \mu\text{m}$	$d / \mu\text{m}$
0	4720	14845	2788	50820	0.1843	20.05	205.1	1508.7	1675
1	3790	11440	2885	51840	0.1948	21.06	210.8	1539.8	1675
2	2880	10032	2886	51841	0.1946	21.07	210.7	1542.2	1675
3	2390	8195	2877	51846	0.1947	21.09	210.6	1543.1	1675
4	1880	6545	2881	51849	0.1942	21.02	210.5	1543.4	1675
5	1539	5895	2882	51852	0.1949	21.05	210.3	1544.5	1675
6	1440	5506	2875	51853	0.1943	21.04	210.2	1543.6	1675
7	1180	5356	2873	51854	0.1944	21.06	210.7	1542.2	1675
24	580	3107	2871	51855	0.1946	21.07	210.9	1542.9	1675
47	280	1608	2882	51857	0.1942	21.08	210.4	1543.4	1675

When approximating the photoconductivity spectra at different voltages using Eq. (1) (Fig. 2), it was noted that with an increase in voltage from 60 to 450 V, the parameter Q_1 increased by a factor of 1.7, Q_2 and Q_3 by a factor of 1.3, and αQ_4 by a factor of 3. This means that with an increase in the electric field strength, the lifetime of carriers in the deeper regions of the sample increases most significantly. The thickness of the first layer increased by a factor of 2 compared to the data in Table I, however, the thicknesses of the remaining layers did not change significantly. Table II shows the values of the parameters of Eq. (1) for approximating the

photoconductivity spectra when focusing the beam near the negative (–) and positive (+) contacts (Fig. 3).

TABLE II. Comparison of positive and negative focusing on Q -values and layer thicknesses

Focusing the beam near the contact	Q_1	Q_2	Q_3	Q_4	$t_1 / \mu\text{m}$	$t_2 / \mu\text{m}$	$t_3 / \mu\text{m}$	$t_4 / \mu\text{m}$	$d / \mu\text{m}$
+	941	4034	1804	0.3938	0.3839	41.15	208.7	1524.6	1675
–	1850	7884	3803	5997	0.2852	61.05	210.8	1503.8	1675

The spectral characteristics of the intrinsic photoconductivity of silver-doped (ZnS:Ag) have been studied. It has been established that the presence of deep defect levels formed within the forbidden band of the crystal plays an important role. The compensation effect influences both the spectral sensitivity and the intensity of photoconductivity.

The photoconductivity mechanism in Ag-compensated ZnS crystals has a complex nature and is determined by the interaction between the band structure and defect-related states. The observed changes in the spectral response are associated with recombination processes involving deep levels. Similar effects have been reported in previous studies of ZnS-based materials, where defect states and surface conditions strongly influence carrier recombination and transport processes. Silver-doped ZnS materials are widely used in electroluminescent panels, CRT phosphors and UV detectors because of their favorable optical and electrical characteristics.

One of the main results of the present study is the appearance of an additional short-wavelength photoconductivity maximum near the fundamental absorption edge after mechanical polishing of the crystal surface. This observation indicates that surface treatment modifies the defect structure in the near-surface region and introduces additional localized states within the band gap. The gradual decrease in the intensity of this maximum with ageing time suggests relaxation or recombination of the surface-related defect states.

The experimental results also show that increasing the applied electric field enhances the photoconductivity signal due to more effective separation and transport of photogenerated charge carriers. In addition, the photoconductivity spectra depend on the position of illumination relative to the electrical contacts, indicating the contribution of carrier injection processes. To explain the experimental observations, a multilayer phenomenological model was used, in which the crystal is considered a system of layers with different recombination properties and carrier lifetimes. This approach makes it possible to describe the depth-dependent behavior of photogenerated carriers in the crystal.

CONCLUSION

The intrinsic photoconductivity spectra of Ag-compensated ZnS crystals exhibit characteristic features associated with electronic transitions near the fundamental absorption edge. In particular, an additional short-wavelength photoconductivity maximum appears after mechanical polishing of the sample surface. Similar surface-related effects have been reported in previous studies on ZnS-based materials, where surface treatment was shown to introduce localized states within the band gap and modify recombination processes.

The observed decrease in the intensity of this maximum with increasing ageing time indicates relaxation of surface defect states. This behavior is in agreement with the literature data, where the evolution of surface states and space charge regions has been shown to influence photoconductivity in II–VI semiconductors.

The experimental results also demonstrate that the photoconductivity depends on the applied electric field and the position of illumination relative to the contacts. The increase in photoconductivity with electric field strength can be attributed to enhanced separation of photogenerated carriers, which is consistent with previously reported results for ZnS and related compounds. In addition, the influence of carrier injection from contacts, leading to recharging of impurity centers, has also been discussed in earlier works.

To interpret the experimental observations, a multilayer phenomenological model was applied, in which the crystal is considered a system of layers with different carrier lifetimes. Such an approach allows one to take into account the depth-dependent behavior of non-equilibrium carriers and the variation of the space charge region near the surface. Similar modelling approaches have been successfully used in the analysis of photoconductivity in compensated semiconductors.

The appearance of the short-wavelength maximum can be attributed to mechanical stresses induced by surface polishing, as well as to the formation of a space charge region influenced by interaction with the ambient atmosphere. The variation of photoconductivity maxima with electric field strength and illumination geometry indicates that the lifetime of non-equilibrium carriers changes with depth, which is consistent with the proposed model.

ИЗВОД

КАРАКТЕРИСТИКЕ СПЕКТАРА СОПСТВЕНЕ ФОТОПРОВОДЉИВОСТИ
ЦИНК-СУЛФИДА ДОПИРАНОГ СРЕБРОМ

KAZIM A. ALIYEV¹, SAADAT O. MAMMADOVA¹, AYTAN N. SULTANOVA¹, ICABIKA Z. SARDAROVA²
и ABDULAGA N. GURBANOV²

¹Baku State University, Baku, Azerbaijan и ²Azerbaijan State Oil and Industry University, Baku, Azerbaijan

Испитивана је сопствена фотопроводљивост цинк-сулфида допираног сребром (ZnS:Ag). Показано је да допирање сребром доводи до значајних модификација у елек-

тронској структури и оптичким својствима ZnS због формирања локализованих енергетских нивоа унутар забрањене зоне. Механичко полирање површине узорка резултира појавом додатног максимума фотопроводљивости близу фундаменталне ивице апсорпције, који постепено нестаје током старења узорка. Ови ефекти се приписују компензацији донорског и акцепторског стања, као и променама у механизмима рекомбинације носилаца наелектрисања. Утврђена је зависност спектра фотопроводљивости од времена старења, примењеног електричног поља и положаја осветљења у односу на контакте. Резултати се објашњавају варијацијама у животном веку неравнотежних носилаца наелектрисања са дубином. Предложен је квалитативни модел који описује спектре фотопроводљивости, узимајући у обзир утицај компензације сребра на енергетску структуру ZnS. Предложени модел пружа увид у фотопроводљиве механизме и подржава развој оптоелектронских материјала на бази ZnS.

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